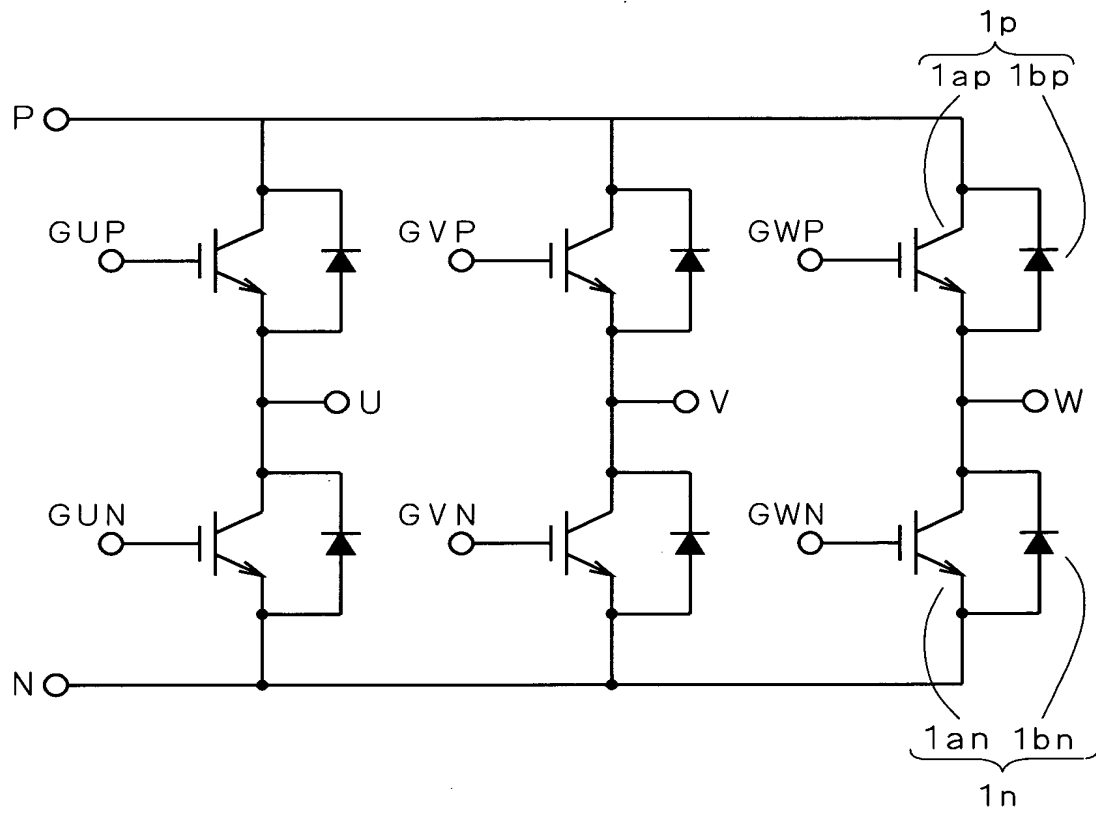
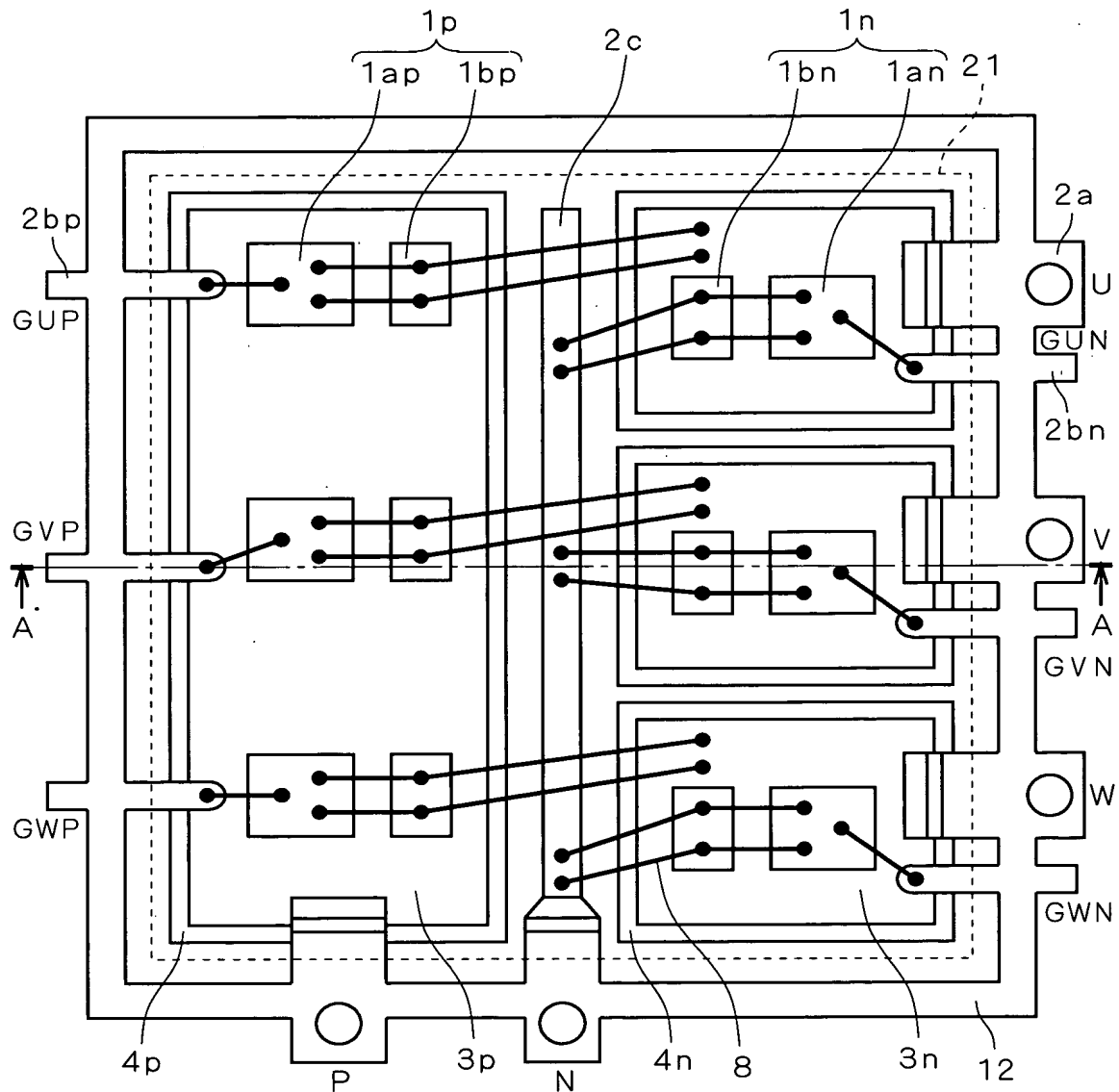


FIG. 1



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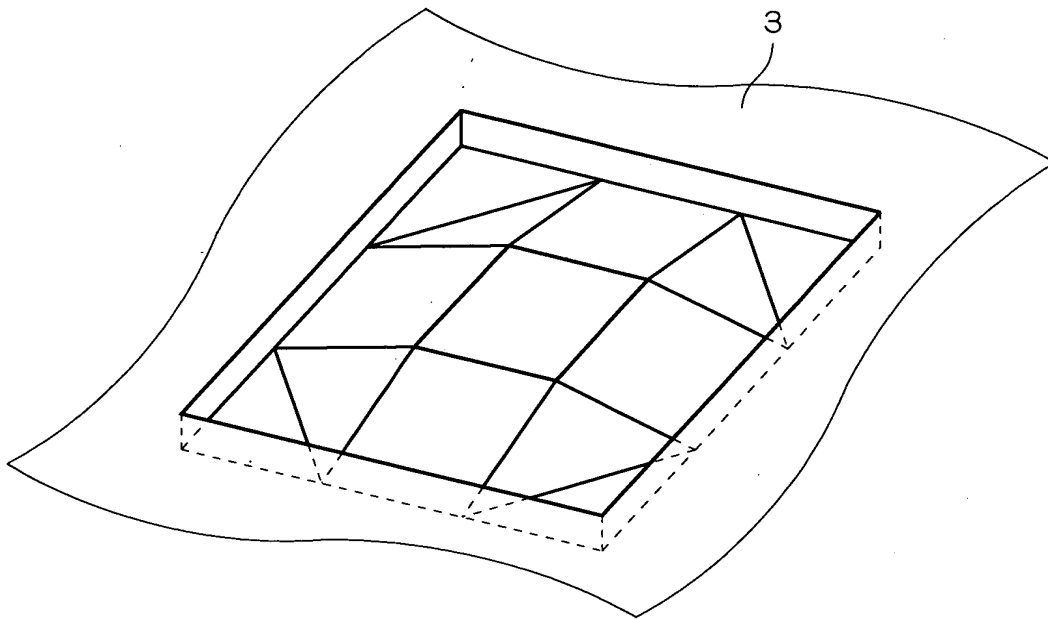
FIG. 2



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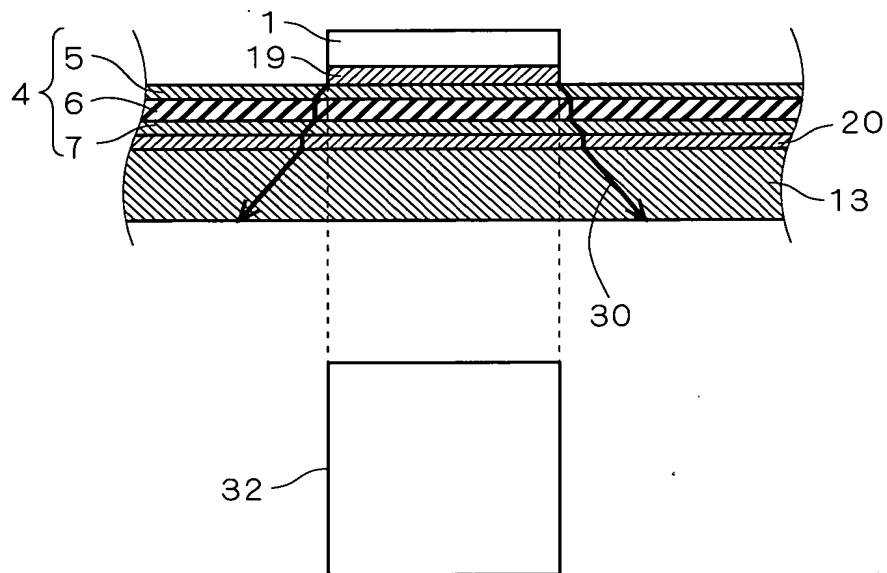
The diagram illustrates a cross-section of a semiconductor device with two main functional regions, 'p' and 'n', separated by a central gate structure. The 'p' region (left) consists of a p-type substrate (3p) with a p-type well (4p) and a p-type body (5p). The 'n' region (right) consists of an n-type substrate (3n) with an n-type well (4n) and an n-type body (5n). Both regions have a gate stack (6p, 6n) and a drain region (7p, 7n). The device is connected to a common drain terminal (2a) and a common source terminal (2b). A central gate terminal (2c) is also shown. Various other components are labeled with numbers 1, 8, 11, and 10.

FIG. 5



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F I G . 6 A



F I G . 6 B

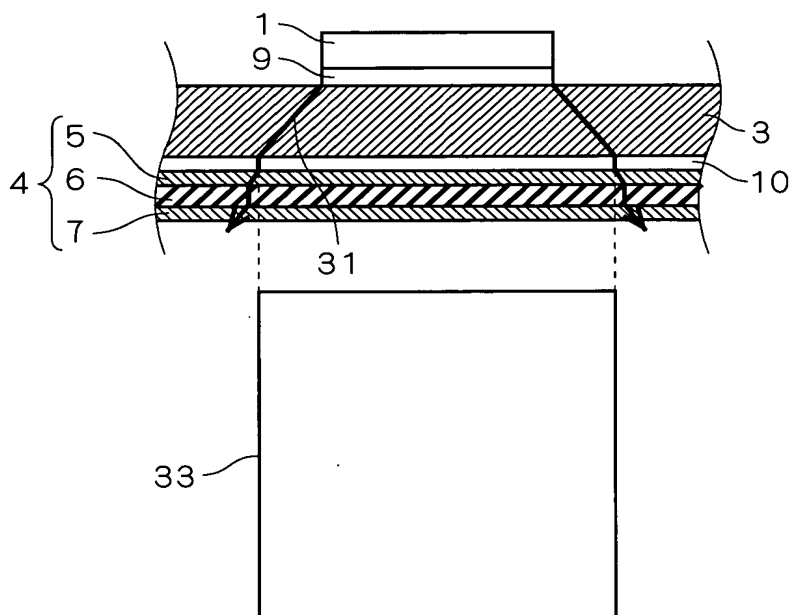
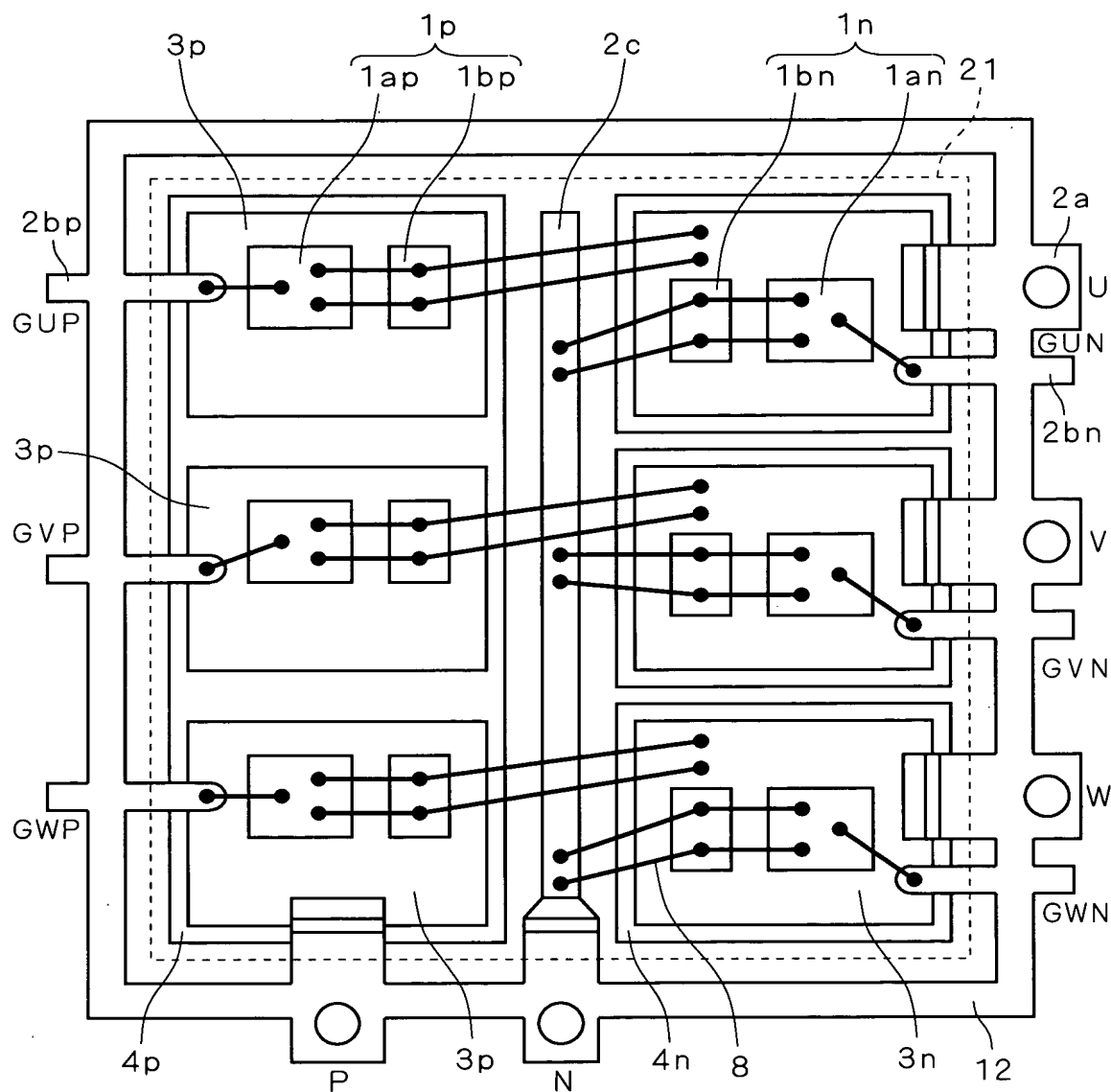
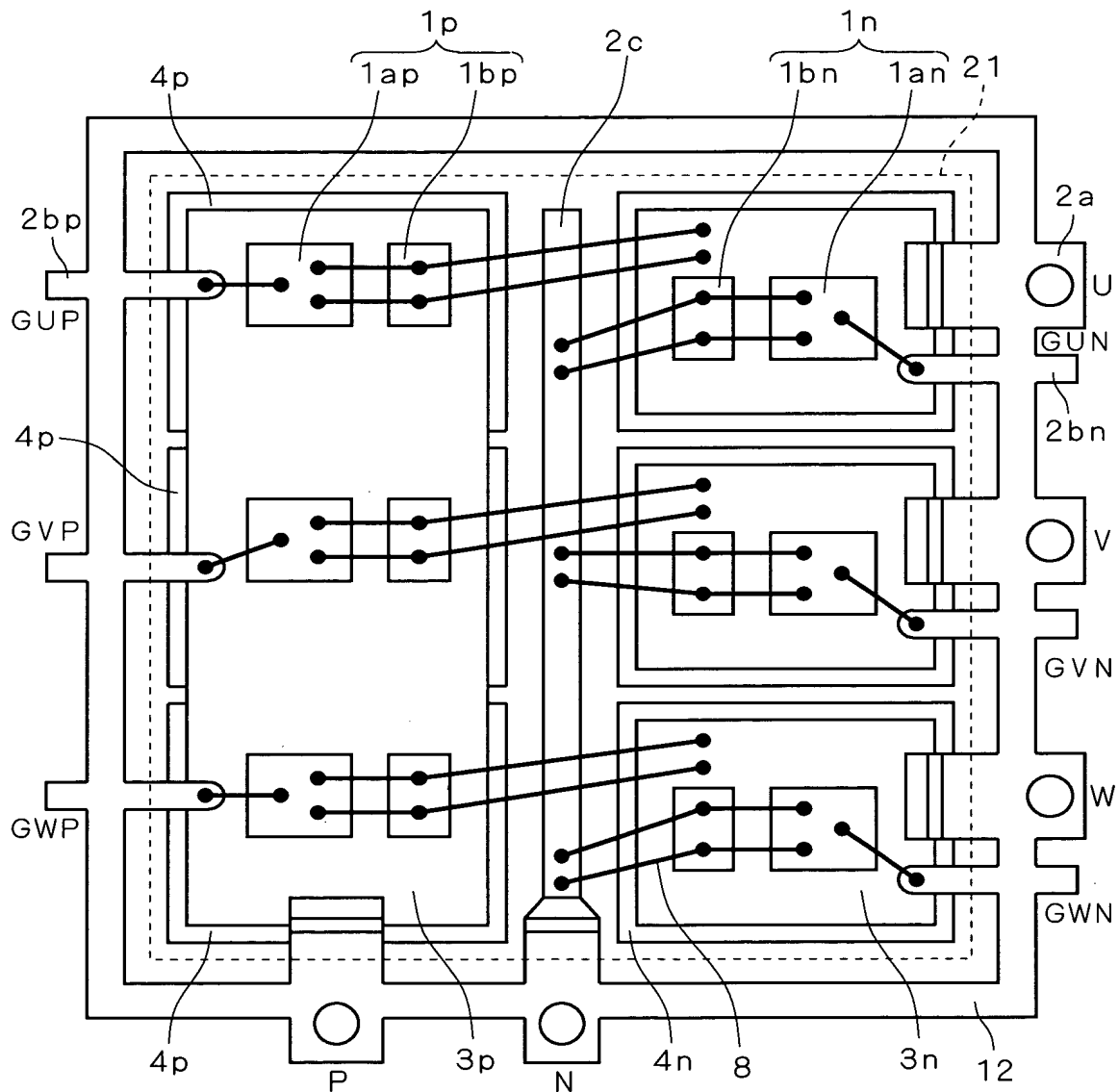


FIG. 7



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F I G . 8



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FIG. 9

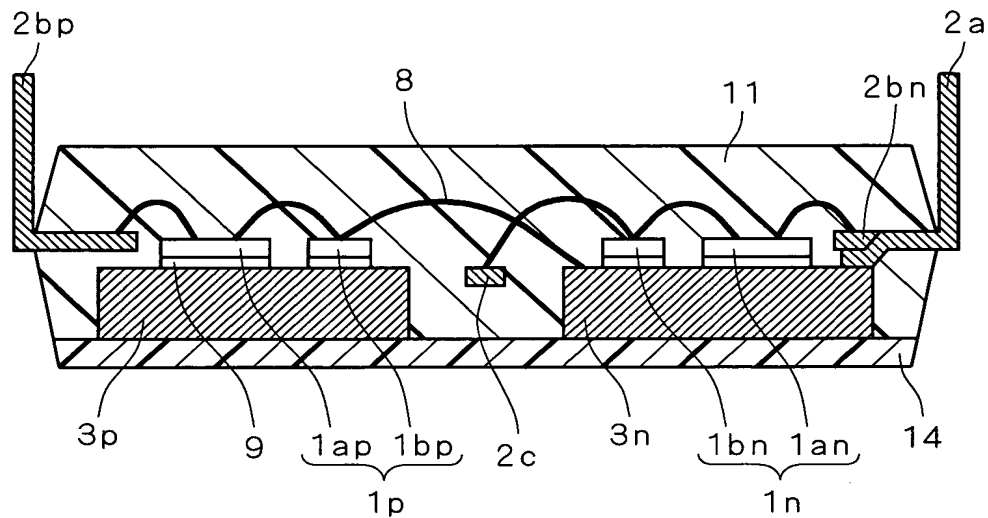


FIG. 10

